

**DMP21D0UFD**

**20V P-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	$I_D$ max $T_A = 25^\circ C$ (Notes 4)
-20V	495m $\Omega$ @ $V_{GS} = -4.5V$	-1.14A
	730m $\Omega$ @ $V_{GS} = -2.5V$	-0.94A
	960m $\Omega$ @ $V_{GS} = -1.8V$	-0.85A
	1300m $\Omega$ @ $V_{GS} = -1.5V$	-0.75A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

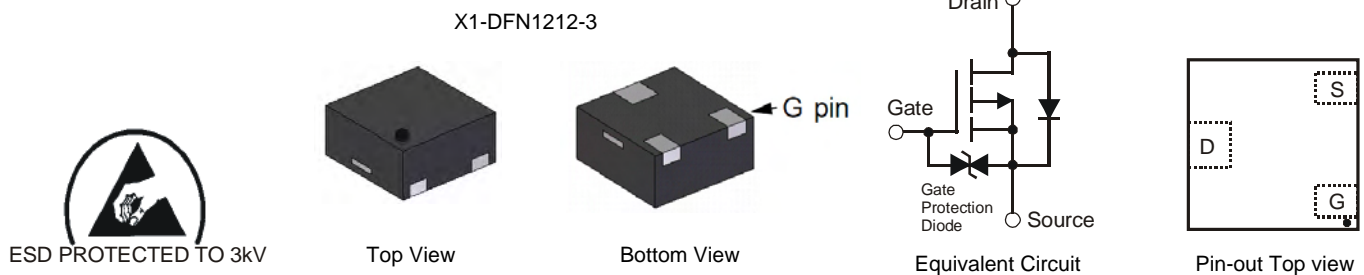
- Portable electronics

**Features and Benefits**

- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate 3KV**
- **Totally Lead-Free & Fully RoHS compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: X1-DFN1212-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.005 grams (approximate)

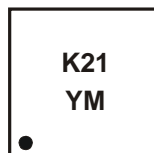


**Ordering Information** (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP21D0UFD-7	K21	7	8	3000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  3. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**



K21 = Product Type Marking Code  
YM = Date Code Marking  
Y = Year (ex: Y = 2011)  
M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	$\pm 8$	V
Continuous Drain Current	Steady State	$T_A = 25^\circ\text{C}$ (Note 4)	$I_D$	-1.14	A
		$T_A = 85^\circ\text{C}$ (Note 4)		-0.83	
		$T_A = 25^\circ\text{C}$ (Note 5)		-0.82	
Pulsed Drain Current (Note 6)			$I_{DM}$	-4.0	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	$P_D$	930	mW
	(Note 5)		490	mW
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	135	$^\circ\text{C/W}$
	(Note 5)		256	$^\circ\text{C/W}$
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
4. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  5. Same as note 4, except the device is mounted on minimum recommended pad layout.
  6. Device mounted on minimum recommended pad layout test board, 10 $\mu\text{s}$  pulse duty cycle = 1%.

**Thermal Characteristics**

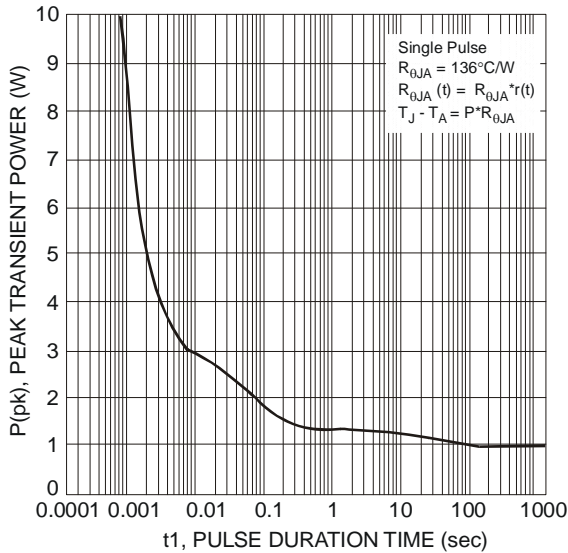


Fig. 1 Single Pulse Maximum Power Dissipation

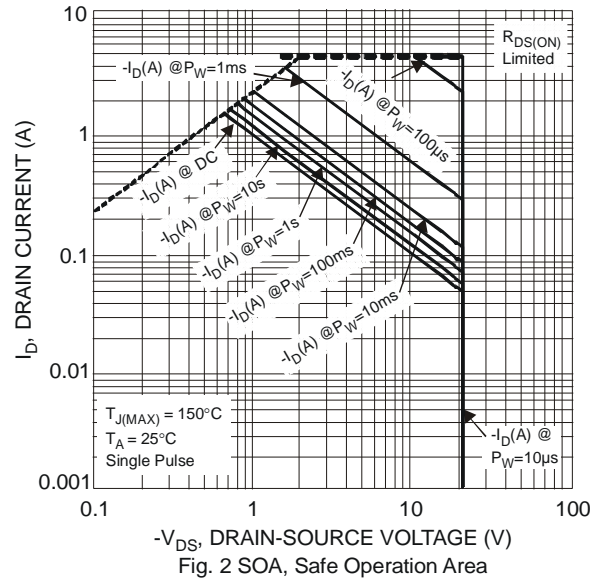


Fig. 2 SOA, Safe Operation Area

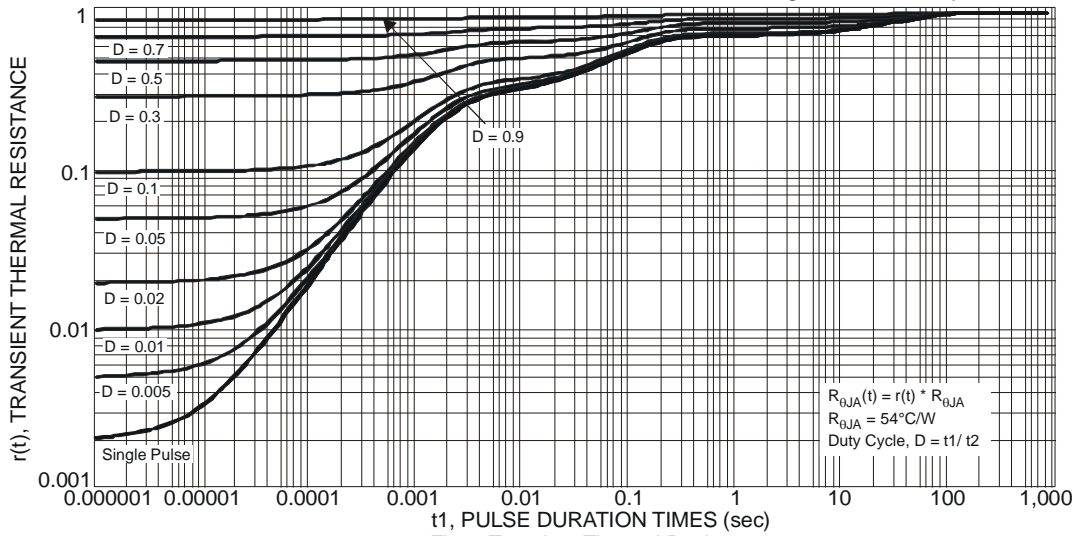


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** @  $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	$I_{DSS}$	-	-	-1	$\mu A$	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu A$	$V_{GS} = \pm 8V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	-0.7	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	-	495	m $\Omega$	$V_{GS} = -4.5V, I_D = -800mA$
				730		$V_{GS} = -2.5V, I_D = -700mA$
				960		$V_{GS} = -1.8V, I_D = -100mA$
				1300		$V_{GS} = -1.5V, I_D = -100mA$
Forward Transfer Admittance	$ Y_{fs} $	50	-	-	mS	$V_{DS} = -3V, I_D = -300mA$
Diode Forward Voltage	$V_{SD}$	-	-	-1.2	V	$V_{GS} = 0V, I_S = -300mA$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	-	76.5	-	pF	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	-	13.7	-	pF	
Reverse Transfer Capacitance	$C_{rss}$	-	10.7	-	pF	
Gate Resistance	$R_g$	-	195	-	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (Note 8)	$Q_g$	-	1.5	-	nC	$V_{GS} = -8V, V_{DS} = -15V, I_D = -1A$
Total Gate Charge (Note 8)	$Q_g$	-	1.0	-	nC	$V_{GS} = -4.5V, V_{DS} = -15V,$ $I_D = -1A$
Gate-Source Charge	$Q_{gs}$	-	0.2	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	0.3	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	7.1	-	ns	$V_{DS} = -10V, -I_D = 1A$ $V_{GS} = -4.5V, R_G = 6\Omega$
Turn-On Rise Time	$t_r$	-	8.0	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	31.7	-	ns	
Turn-Off Fall Time	$t_f$	-	18.5	-	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guarantee by design.

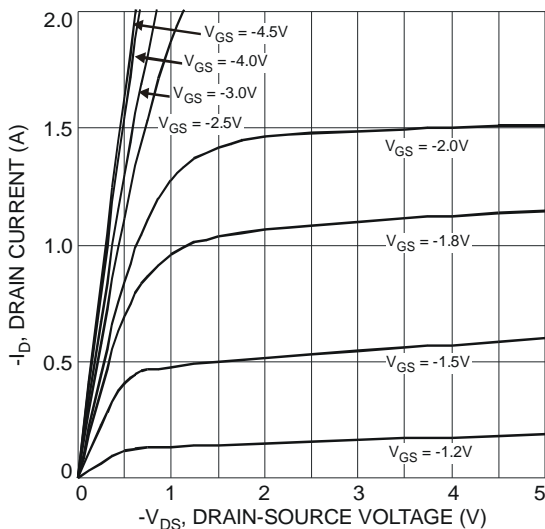


Fig. 4 Typical Output Characteristic

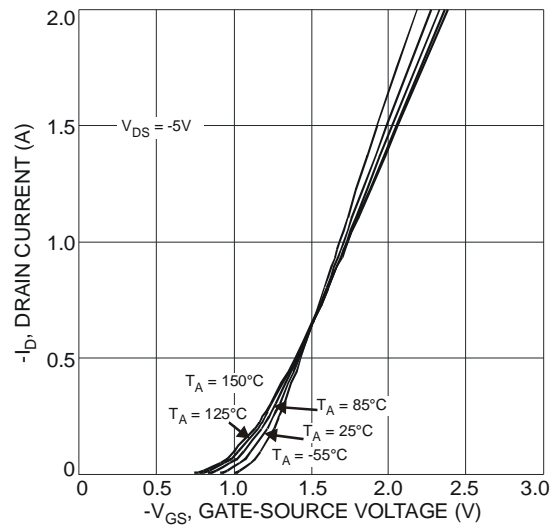


Fig. 5 Typical Transfer Characteristic

**DMP21D0UFD**

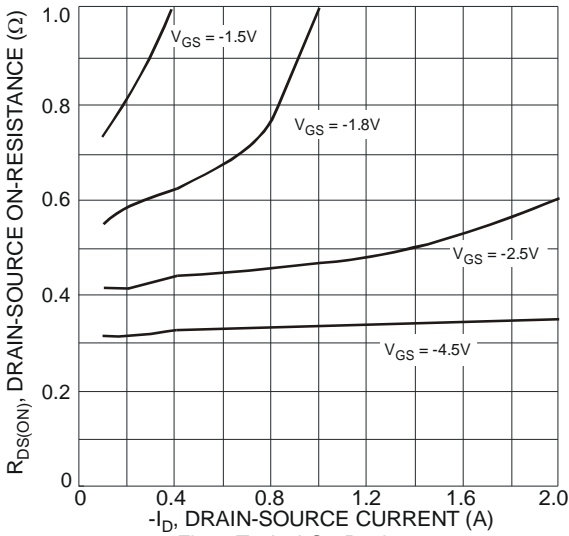


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

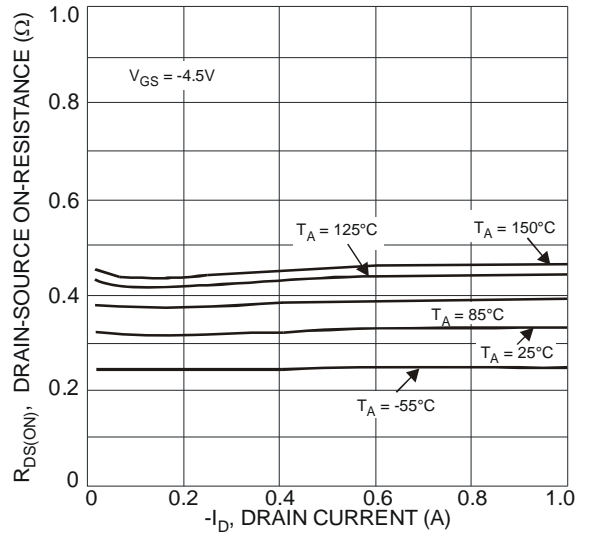


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

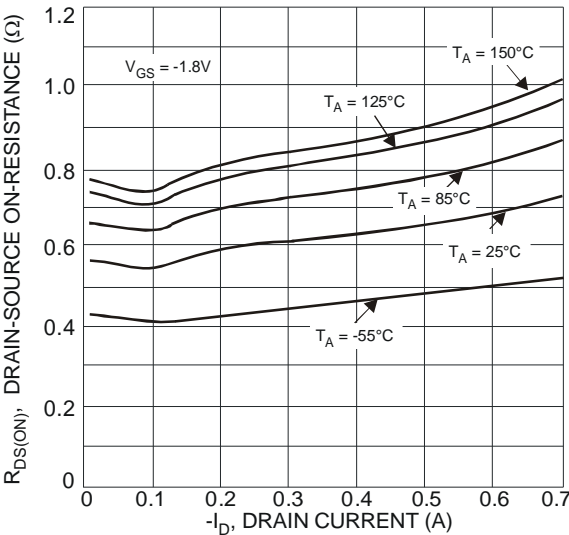


Fig. 8 Typical On-Resistance vs. Drain Current and Temperature

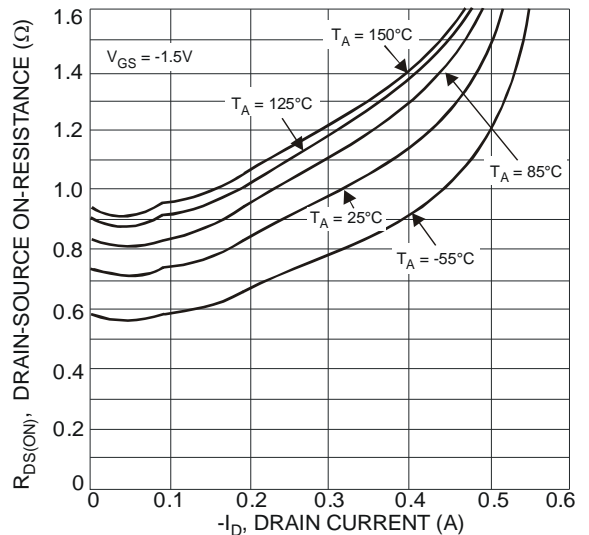


Fig. 9 Typical On-Resistance vs. Drain Current and Temperature

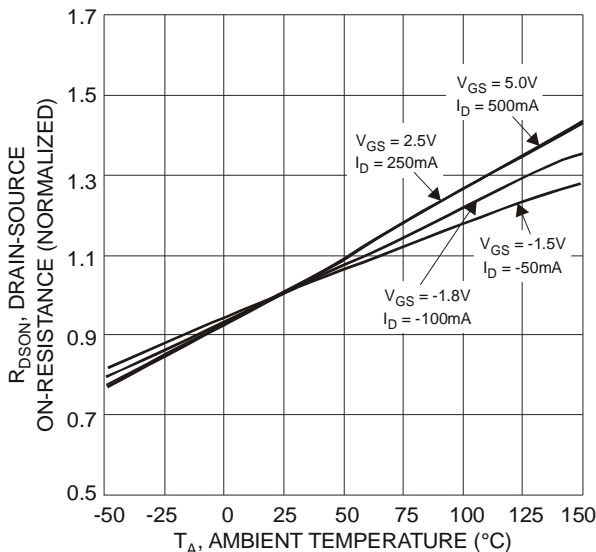


Fig. 10 On-Resistance Variation with Temperature

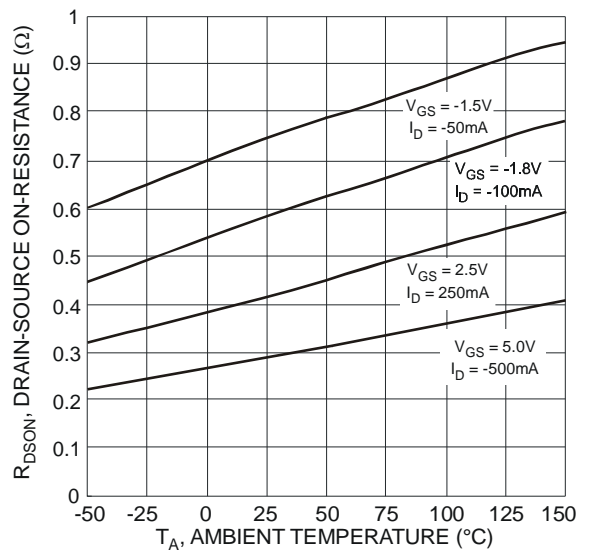


Fig. 11 On-Resistance Variation with Temperature

**DMP21D0UFD**

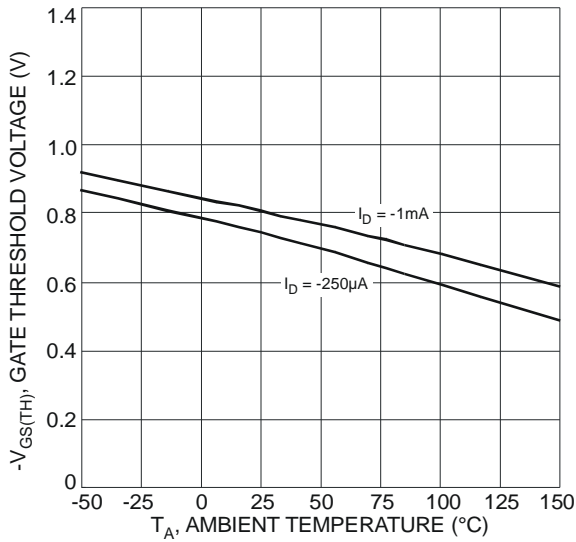


Fig. 12 Gate Threshold Variation vs. Ambient Temperature

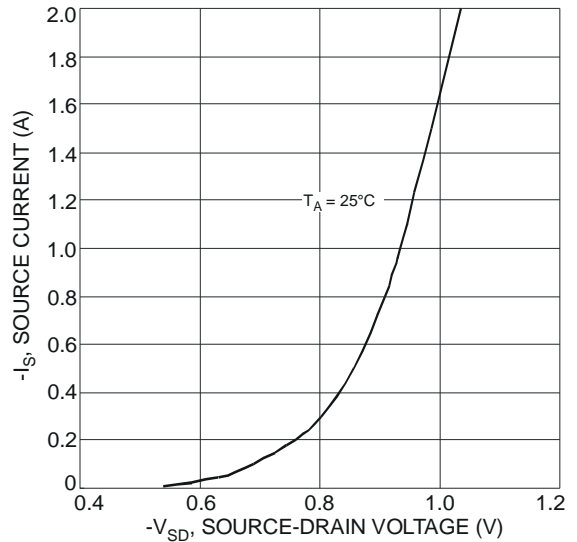


Fig. 13 Diode Forward Voltage vs. Current

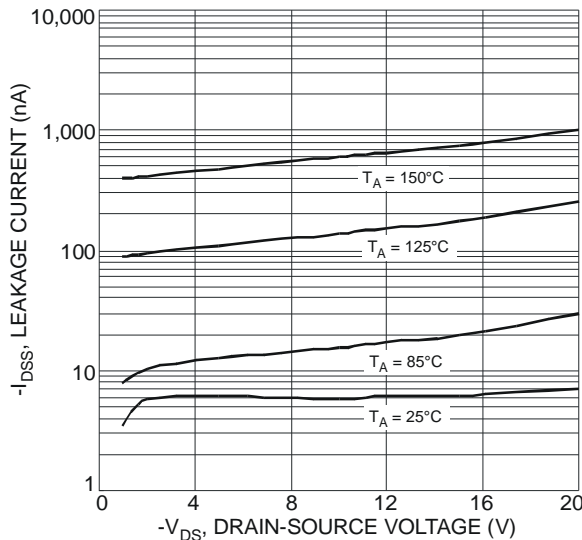


Fig. 14 Typical Leakage Current vs. Drain-Source Voltage

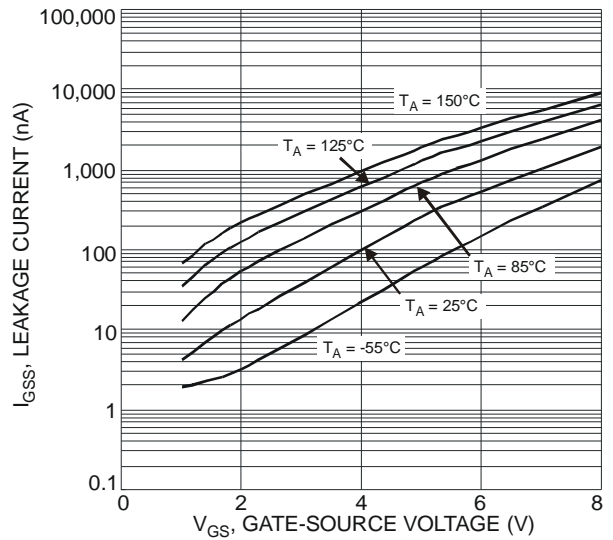


Fig. 15 Leakage Current vs. Gate-Source Voltage

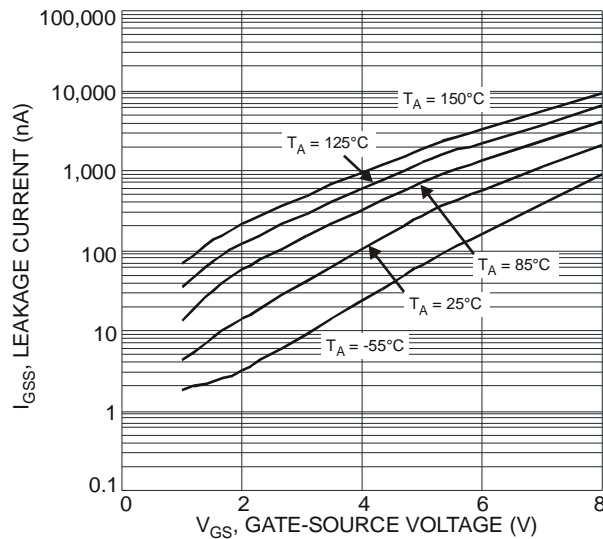


Fig. 16 Leakage Current vs. Gate-Source Voltage

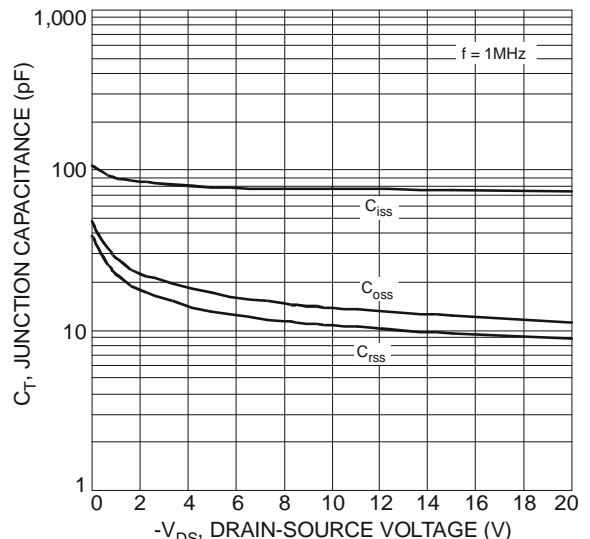


Fig. 17 Typical Junction Capacitance

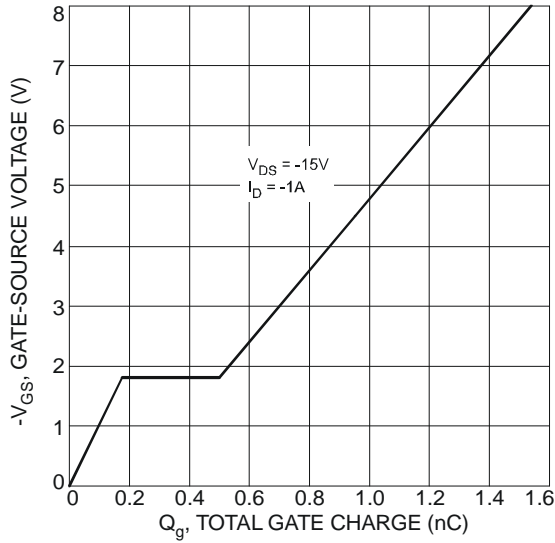
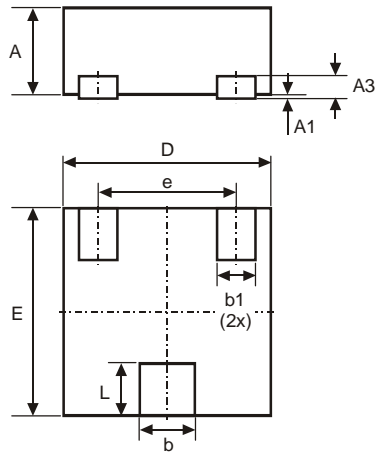


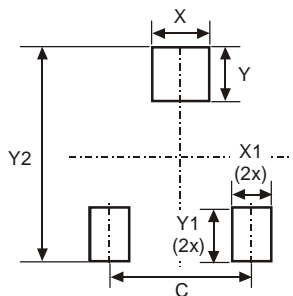
Fig. 18 Gate-Charge Characteristics

### Package Outline Dimensions



X1-DFN1212-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
E	1.15	1.25	1.20
e	-	-	0.80
L	0.25	0.35	0.30
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	0.80
X	0.42
X1	0.32
Y	0.50
Y1	0.50
Y2	1.50

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